Transistor delivers 280-watt pulsed power

RF Micro Devices today announced the release of the RFHA1025, a highly-efficient 280-watt pulsed gallium nitride (GaN) RF matched power transistor. The RFHA1025 delivers superior performance versus competing silicon power technologies.

RFMD’s RFHA1025 complements the recently released 380-watt RF3928B, the highest output power S-Band device in RFMD’s matched power transistor family. RFMD is expanding its portfolio of GaN-based power amplifier transistor products across bands, increasing its leadership position in the radar market.

RFMD's GaN matched power transistors extend range, reduce size and weight, and improve overall ruggedness in new and existing radar architectures. The RFHA1025 operates over a broad frequency range (0.96-1.2GHz) and delivers 280-watt pulsed power, high gain >14dB, and high peak efficiency of >55%. Additionally, the RFHA1025 incorporates internal matching to simplify and shrink designers’ circuits. Packaged in a hermetic, flanged ceramic package, the RFHA1025 leverages RFMD's advanced heat sink and power dissipation technologies, delivering excellent thermal stability and conductivity. RFMD’s RF393x unmatched power transistors (UPT) can be used as drivers to the RFHA1025.

Jeff Shealy, general manager of RFMD's Power Broadband Business Unit, said, "RFMD is pleased to expand our GaN-based product portfolio, offering industry-leading power performance in support of diverse end markets. RFMD's GaN product portfolio demonstrates our commitment to technology and product leadership, and we look forward to introducing additional GaN devices in the near term that feature superior power density, high power efficiency, and rugged dependability."

RFMD is exhibiting its GaN power portfolio at the IEEE International Microwave Symposium through June 22, in Booth 1210 at the Palais des congress, in Montreal, Canada.

Availability

Samples and production quantities are available now through RFMD’s online store or through local RFMD sales channels.

For more information, please visit RFMD's web site at www.rfmd.com [1].

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[1] http://www.rfmd.com